

TITLE OF THE INVENTION

NONVOLATILE SEMICONDUCTOR MEMORY DEVICE AND NONVOLATILE
SEMICONDUCTOR MEMORY SYSTEM

CROSS-REFERENCE TO RELATED APPLICATIONS

5 This application is based upon and claims the
benefit of priority from the prior Japanese Patent
Application No. 2000-301063, filed September 29, 2000,
the entire contents of which are incorporated herein by
reference.

10 BACKGROUND OF THE INVENTION

1. Field of the Invention

The present invention relates to an electrically
rewritable nonvolatile semiconductor memory device, and
a system thereof.

15 2. Description of the Related Art

A conventional flash memory has a digital control
interface. Then, in addition to a digital control
signal terminal, the flash memory has a power source
terminal, and a writing and erasing power source
20 terminal. These are DC inputs, which are controlled in
accordance with a digital control signal from the
outside inside of the flash memory to be rectified into
an appropriate waveform and applied to a memory cell.
As a consequence, a large number of control circuits
25 which are referred to as peripheral circuits are
provided in addition to the memory cells in order to
create a signal required for the reading, writing, and

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erasing of the memory cell inside of the flash memories.

Conventionally, a large number of peripheral circuits are formed in a chip for creating a signal required for the reading, writing, and erasing of the memory cell inside of the flash memory with the result that the chip size is enlarged and a cost thereof is increased. However, when an attempt is made to directly control the memory cell from the outside, an outside wiring load is increased.

Furthermore, conventionally, a large number of detachable memory devices are provided which use a flash memory. For example, a smart medium, a compact flash, a memory stick, an SD card or the like is provided. An interface of the smart medium is the interface itself of a NAND flash memory. Other devices are similar to the interface of a magnetic storage device. In any way, like the magnetic memory device, file data and a logical address are received and memorized under the file control on the host side. A file control system is required on the host side.

In this manner, the conventional memory device using the flash memory is controlled under the file control on the host side, so that the performance thereof is deteriorated. For example, when the minimum rewriting unit of the flash memory is larger than the minimum unit of the file control on the host side, it is required to rewrite even the file data which is not

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required to be rewritten inside of the flash memory at the time of rewriting one piece of file data. However, when an attempt is made to conduct the file control on the side of the flash memory system, there arises a problem as to how the interface is dealt with.

BRIEF SUMMARY OF THE INVENTION

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10 A semiconductor integrated circuit device according to an embodiment of the present invention comprises: a first semiconductor substrate, in which, a memory cell array including a plurality of nonvolatile semiconductor memory cells, a plurality of bit lines electrically connected to the memory cell array, a plurality of word lines electrically connected to the memory cell array, a plurality of input terminals, and

15 a plurality of transfer gate transistors each having one end electrically connected to a corresponding one of the word lines and another end electrically connected to a corresponding one of the input terminals, are provided; and a second semiconductor

20 substrate, in which, a plurality of output terminals electrically connected to the input terminals of the first semiconductor substrate, and a word line control circuit configured to control the word lines and electrically connected to the output terminals, are

25 provided.

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A nonvolatile semiconductor memory system according to an embodiment of the present invention

comprises: a memory having a memory cell array including a plurality of nonvolatile semiconductor memory cells; a control portion configured to control the memory; a network interface connectable to a network; a file management portion connected to the network interface configured to manages a relation between a data file given from the network and an address of the memory cell array; and a memory interface connected to the file management portion configured to convert a signal given from the network to a signal which capable of used at the control portion.

A nonvolatile semiconductor memory device according to an embodiment of the present invention comprises: a first semiconductor substrate, in which, a memory having a memory cell array including a plurality of nonvolatile semiconductor memory cells, is provided; and a second semiconductor substrate, in which, a control portion configured to control the memory, a network interface connectable to a network, a file management portion connected to the network interface configured to manages a relation between a data file given from the network and an address of the memory cell array, and a memory interface connected to the file management portion configured to convert a signal given from the network to a signal which capable of used at the control portion, are provided.

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BRIEF DESCRIPTION OF THE SEVERAL VIEWS OF THE DRAWING

FIG. 1 is a view showing one example of a package of a nonvolatile semiconductor memory device according to a first embodiment of the present invention.

5 FIG. 2 is a view showing one example of an inside of the package 1 shown in FIG. 1.

FIG. 3 is a view showing one example of a stacked chip structure inside of the package 1 shown in FIG. 1.

10 FIG. 4 is a view showing one example of an inside of a package 4 shown in FIGS. 2 and 3.

FIG. 5 is a view showing one example of a connection structure between the terminal 8 and the terminal 3 shown in FIG. 4.

15 FIG. 6 is a view showing one example of a connection structure between the terminal 8 and the terminal 7 shown in FIG. 4.

FIG. 7 is a view showing one example of an inside of the package 5 shown in FIGS. 2 and 3.

20 FIG. 8 is a block diagram showing one example of circuits formed in the semiconductor substrate 9 inside of the package 4.

FIG. 9 is a block diagram showing one example of circuits formed in a semiconductor substrate 12 inside of the package 5.

25 FIG. 10 is a view showing one example of the memory cell array 25 shown in FIG. 9.

FIG. 11A is a sectional view showing a cross

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section taken along the bit line BL of the memory cell M shown in FIG. 10.

FIG. 11B is a sectional view showing a cross sectional taken along the word line WL of the memory cell M.

FIG. 11C is a sectional view taken along the select gate line SG of the select transistor S shown in FIG. 10.

FIGS. 12, 13, 14, 15 and 16 are a circuit diagram showing one example of a signal conversion circuit 31, respectively.

FIG. 17 is a circuit diagram showing one example of a circuit structure of the block selection circuit 26.

FIG. 18 is a circuit diagram partially showing one example of a shift register in the block selection circuit 26.

FIG. 19 is a circuit diagram showing one example of the shift register in the block selection circuit 26.

FIG. 20 is a circuit diagram showing one example of a shift register circuit in a data circuit 27.

FIG. 21 is a circuit diagram showing one example of the data circuit 27, the bit line circuit 28 and the bit line BL.

FIG. 22 is a circuit diagram showing another example of the signal conversion circuit 31.

FIG. 23 is a circuit diagram showing one example

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of the source line circuit 29 and the well circuit 30.

FIG. 24 is a system diagram showing one example of a system of the nonvolatile memory device according to the first embodiment of the present invention.

5 FIG. 25A is a view showing another example of an inside of the package 1 shown in FIG. 1.

FIG. 25B is a view showing another example of the stacked chip structure.

10 FIG. 26 is a system diagram showing one example of a nonvolatile semiconductor memory device system according to a second embodiment of the present invention.

15 FIG. 27 is a view showing one example of a relation between the network and the nonvolatile memory device shown in FIG. 26.

FIG. 28 is a view showing one example of another relation between the network and the nonvolatile memory device shown in FIG. 26.

DETAILED DESCRIPTION OF THE INVENTION

20 Hereinafter, embodiments of the present invention will be explained by referring to the drawings. In this explanation, common portions are denoted by common reference numerals over the whole drawings.

(First Embodiment)

25 FIG. 1 is a view showing one example of a package of a nonvolatile semiconductor memory device according to a first embodiment of the present invention.

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As shown in FIG. 1, signal terminals 2 are provided on a surface of a package 1.

FIG. 2 is a view showing one example of an inside of the package 1 shown in FIG. 1.

5 As shown in FIG. 2, inside of the package 1, a package 4 and eight packages 5-0 to 5-7 are provided. The packages 4 and 5-0 to 5-7 each sealed a semiconductor substrate. The package 4 is stacked on the package 5-0. The package 5-0 is stacked on the
10 package 5-1. The package 5-1 is stacked on the package 5-2. The package 5-6 is stacked on the package 5-7. On the side surfaces of the respective packages 4, 5-0 to 5-7, wirings 6 are provided for mutually connecting terminals provided on the respective packages.

15 On the rear surface of the lamination layer of the package 4, another terminals 3 are further provided to be connected to the signal terminals 2 provided on the package 1.

FIG. 3 is a view showing one example of a stacked
20 chip structure inside of the package 1 shown in FIG. 1.

As shown in FIG. 3, terminals 7 are provided on respective side surfaces of the packages 4, 5-0 to 5-7 and the respective terminals 7 are mutually connected with the wirings 6.

25 FIG. 4 is a view showing one example of an inside of the package 4 shown in FIGS. 2 and 3.

As shown in FIG. 4, a semiconductor substrate 9 is

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sealed inside of the package 4. Terminals 8 are provided on the surface of the substrate 9 the terminals to be connected to the terminals 3 and the terminals 7.

5 FIG. 5 is a view showing one example of a connection structure with the terminal 8 and the terminal 3 shown in FIG. 4.

10 As shown in FIG. 5, the terminal 8 provided on the surface of the semiconductor substrate 9 is connected to the terminal 3 formed on the rear surface of the lamination layer of the package 4 with a wiring material 10 filled into a hole formed on the package 4.

15 FIG. 6 is a view showing one example of a connection structure of the terminal 8 and the terminal 7 shown in FIG. 4.

As shown in FIG. 6, the terminal 8 provided on the surface of the substrate 9 is connected to the terminal 7 formed on the side surface of the package 4 with a bonding wire 11.

20 FIG. 7 is a view showing one example of an inside of the package 5 shown in FIGS. 2 and 3.

25 As shown in FIG. 7, a semiconductor substrate 12 is sealed inside of the package 5. Terminals 8 are provided on the surface of the substrate 12 to be connected to the terminals 7 with the connection structure shown in FIG. 6. A nonvolatile semiconductor memory cell array is formed in the substrate 12 as

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explained later.

FIG. 8 is a block diagram showing one example of circuits formed in the semiconductor substrate 9 inside of the package 4.

5 As one example of the terminals 8 to be connected to the terminals 3, OP, RB, REN, CEN, Vcc, Vss, CLEN, ALEN, WEN, WPn, and IO0 to IO7 terminals are shown in FIG. 8. Symbol Vcc denotes a power source terminal, and symbol Vss denotes a ground terminal. Input and
10 output terminals IO0 to IO7 are terminals for the input and output of written and read data, and for the input of command data and address data. The terminals IO0 to IO7 are connected, for example, to a data input and output buffer 13. OP, RB, REN, CEN, CLEN, ALEN, WEN, and WPn terminals are terminals for the input of
15 control signals OP, RB, REN, CEN, CLEN, ALEN, WEN, and WPn and are connected, for example, to a control input buffer 14. The Signals of the terminals 3 function as terminals as seen, for example, in the NAND flash
20 memory TC58V32AF (manufactured by Toshiba Corporation).

A state machine 15 is a circuit for generating a basically control signal for controlling the circuits in the package 5 in accordance with a control signal, a command and an address input from the outside.

25 The state machine 15 shown in FIG. 8 which controls, as one example, an address control circuit 16, a voltage generation circuit 17, a chip selection

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circuit 18, a block selection control circuit 19, a word line control circuit 20, a data control circuit 21, a bit line control circuit 22, a source line control circuit 23, and a well control circuit 24. The address control circuit 16 manages an address at the time of an access to the memory cell array inside of the package 5. The voltage generation circuit 17 generates a voltage required for the reading, writing and erasing of data from the memory cell array inside of the package 5. The chip selection circuit 18 selects the package 5, for example, any of the packages 5-0 through 5-7. The block selection control circuit 19 selects a memory block of the memory cell array inside of the package 5. The word line control circuit 20 controls word lines connected to the memory cell array inside of the package 5. The data control circuit 21 controls the input and output of the data with the memory cell array inside of the package 5. The bit line control circuit 22 controls bit lines connected to the memory cell array inside of the package 5. The source line control circuit 23 controls source lines connected to the memory cell array inside of the package 5. The well control circuit 24 controls a semiconductor layer (well) in which the memory cell array inside of the package 5 is formed.

Furthermore, as one example of the terminals 8 to be connected to the terminals 7, SG1, CG0, CG1, CG2,

CG3, SG2, SGB, Vcc, Vss, CE0, CE1, CE2, CE3, CE4, CE5, CE6, CE7, PGM, SEN, CK0, CK1, OUT0, OUT1, IN0, IN1, Well, Vpp, OSC, RA, RB, RST, SRC, OD, EV, BS, PRE, and VH terminals are shown in FIG. 8.

5 A ROM 100 stores an address of a defect memory cell of the memory cell array inside of the package 5. The address control circuit 16 refers to data of the ROM 100 so that the defect memory cell is not used.

10 FIG. 9 is a block diagram showing one example of circuits formed in the semiconductor substrate 12 inside of the package 5.

15 As shown in FIG. 9, a nonvolatile semiconductor memory device, for example, a flash memory is formed in the substrate 12 inside of the package 5. Furthermore, as one example of the terminals 8 to be connected to the terminals 7, SG1, CG0, CG1, CG2, CG3, SGB2, SGB, Vcc, Vss, CE0, CE1, CE2, CE3, CE4, CE5, CE6, CE7, PGM, SEN, CK0, CK1, OUT0, OUT1, IN0, IN1, Well, Vpp, OSC, RB, RA, RB, RST, SRC, OD, EV, BS, PRE, and VH terminals are shown in FIG. 9. These terminals 8 are connected to the terminals 8 having the same name inside of the package 4 via the wiring 6.

25 As one example, a memory cell array 25, a block selection circuit 26, a data circuit 27, a bit line circuit 28, a source line circuit 29, a well circuit 30, and a signal conversion circuit 31 are provided in the substrate 12. The nonvolatile semiconductor memory

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cell is arranged in the memory cell array 25, for example, in a matrix-like configuration. The block selection circuit 26 selects a memory block of the memory cell array 25. The data circuit 27 controls the input and output of the data with the selected memory cell. The bit line circuit 28 controls a voltage of the bit line connected to the memory cell array 25. The source line control circuit 29 controls the source line connected to the memory cell array 25. The well circuit 30 controls a well in which the memory cell array 25 is formed. The signal conversion circuit 31 converts a signal of the terminal 8 and an inside signal.

FIG. 10 is a view showing one example of the memory cell array 25 shown in FIG. 9.

As shown in FIG. 10, the memory cell array 25 is divided into, for example, sixteen memory blocks BLOCK0 to BLOCK15. Each of the memory blocks BLOCK_i (i=0 to 15) is provided with four word lines WL0-i to WL3-i and two select gate line SGD-i and SGD-i.

Four memory cells M and two select transistors S are connected to each other in series to constitute a NAND type memory cell unit. One end of the NAND type memory cell unit is connected to bit lines BLe0 to BLe7, and BLo0 to BLo7 while the other end thereof is commonly connected to a source line Source. Here, for simplification, the number of memory cells is decreased.

However, when one word line comprises 4224 memory cells or more (528 bytes or more), one block comprises 16 word lines, and one memory cell array comprises 512 blocks or more, a memory cell array comparable to the NAND flash memory TC58V32AFT can be provided.

FIGS. 11A, 11B, and 11C are views showing one example of a structure of a memory cell M, respectively. FIG. 11A is a sectional view showing a cross section taken along the bit line BL of the memory cell M shown in FIG. 10. FIG. 11B is a sectional view showing a cross sectional taken along the word line WL of the memory cell M. FIG. 11C is a sectional view taken along the select gate line SG of the select transistor S shown in FIG. 10.

As shown in FIG. 11A, there is shown a view showing a structure of the memory cell M. An n-type well 32 is formed in a p-type semiconductor substrate 12, and a p-type well 34 is formed inside thereof. An n-type diffusion layer 35 and a p-type diffusion layer 33 are formed in the surface portion of the semiconductor substrate 12. A floating gate FG is stacked via the semiconductor substrate 12 and a tunnel oxide film and a control gate which forms a word line WL via an insulation film is stacked thereon. The bit line BL is formed of a second metal material and is connected to a first metal material M0 via a V1 contact. Furthermore, the bit line BL is connected to the n-type

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diffusion layer 35 which forms and end of a NAMD memory unit via the CB contact.

Furthermore, as shown in the cross sections of FIG. 11B and 11C, each of the memory cells M id
5 mutually isolated with s device isolation STI (shallow trench isolation) in a direction along the word line WL.

FIGS. 12 to 16 are circuit diagrams showing one example of a signal conversion circuit 31, respectively.

As shown in FIG. 12, one of the terminals CE0 to
10 CE7 is input to the inverter 10 to be output as CEns. CEns are output as CEs via the inverter 11. Incidentally, in FIG. 12, CE0 is noted and shown. In the first embodiment, since there are provided eight packages 5, for example, and one of the terminals CE0
15 to CE7 is input to the inverter 10 to be output as CEns without being overlapped in each of the packages. With the chip selection signals CE0 to CE7, any one is selected out of the packages 5-0 to 5-7.

Signals CK0 and CK1 shown in FIG. 13 become
20 effective when the chip selection signal CEs are set to "H" and are converted to CK0s, CK0sn, CK1s and CK1sn.

Signals RST, RA, RB, OSC, SEN, IN0, and IN1 shown in FIG. 14 become effective when the chip selection signal CEs is set to "H" and are converted to RSTs, RAs, RBs, OSCs, SENs, IN0s, and IN1s.
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Signals OD, EV, PRE, and PGM shown in FIG. 15 become effective when the chip selection signal CEs is

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set to "H", and are converted to ODs, EVs, PREs, and PGMs with voltage amplitude of V_H .

Internal signals OUT0s and OUT01s shown in FIG. 16 are output as OUT0 and OUT1 from the OUT0 and OUT1 terminals when the chip selection signal CEs is set to "H".

FIG. 17 is a circuit diagram showing one example of a circuit structure of the block selection circuit 26. The circuit shown in FIG. 17 is provided, for example, on each of the block.

As shown in FIG. 17, the word lines WL0-i to WL3-i and the select gate lines SGD-i and SGS-i of the BLOCKi are linked to the terminals CG0, CG1, CG2, CG3, SG1 and SG2 via an n-type MOS (NMOS) transistors Qn17, Qn16, Qn15, Qn14, Qn12, and Qn18, respectively.

Furthermore, the select gate lines SGD-i and SGS-i are connected to the terminal SGB via Qn13 and Qn19. In the selected block, a node TransferG is set to a voltage of about V_{pp} , and the word line and the select gate line are controlled with signals CG0, CG1, CG2, CG3, SG1 and SG2 from the package 4. In the unselected block, the TransferG is grounded, the word line is set to a floating state, and the select gate line is controlled with the SGB.

The block is selected with signals RA-j and RB-k, respectively. When the RA-j and RA-k are both set to "H", the block is selected. The signal OSCs is

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synchronized with an emit signal OSC generated in the package 4 to drive a pumping circuit comprising NMOS transistors Qn8, Qn9 and Qn10 and a depletion type NMOS transistor Qd0. As a consequence, Vpp is transferred to the TransferG. Correspondence between each of the blocks and the signal RA-j/RB-k is shown in Table 1.

Table 1

BLOCK 0	RA-0	RB-0
BLOCK 1	RA-1	RB-0
BLOCK 2	RA-2	RB-0
BLOCK 3	RA-3	RB-0
BLOCK 4	RA-0	RB-1
BLOCK 5	RA-1	RB-1
BLOCK 6	RA-2	RB-1
BLOCK 7	RA-3	RB-1
BLOCK 8	RA-0	RB-2
BLOCK 9	RA-1	RB-2
BLOCK10	RA-2	RB-2
BLOCK11	RA-3	RB-2
BLOCK12	RA-0	RB-3
BLOCK13	RA-1	RB-3
BLOCK14	RA-2	RB-3
BLOCK15	RA-3	RB-3

Each voltage when the BLOCKi is selected is shown in Table 2.

Table 2

	Erase	Write	Read	Write verify
SGS-i	Vera	0V	Vread	Vread
WL0-i	0V	Vpass	Vread	Vread
WL1-i	0V	Vpgm	Vcgr	Vcgv
WL2-i	0V	Vpass	Vread	Vread
WL3-i	0V	Vpass	Vread	Vread
SGD-i	Vera	Vcc	Vread	Vread
SGS-x(x≠i)	Vera	0V	0V	0V
WL0-x(x≠i)	Vera	0V	0V	0V
WL1-x(x≠i)	Vera	0V	0V	0V
WL2-x(x≠i)	Vera	0V	0V	0V
WL3-x(x≠i)	Vera	0V	0V	0V
SGD-x(x≠i)	Vera	0V	0V	0V
SGB	Vcc	0V	0V	0V
SG2	Vcc	0V	Vread	Vread
CG0	0V	Vpass	Vread	Vread
CG1	0V	Vpgm	0V	0.5V
CG2	0V	Vpass	Vread	Vread
CG3	0V	Vpass	Vread	Vread
SG1	Vcc	Vcc	Vread	Vread
BL (selected) (data "0")	-	0V	Vcc	Vcc
BL (selected) (data "1")	-	Vcc	0V	0V
BL (unselected)	Vera	Vcc	0V	0V
BS	Vcc	Vcc	0V	0V
Source	Vera	0V	0V	0V
SRC	Vera	0V	0V	0V
CPWELL	Vera	0V	0V	0V
Well	Vera	0V	0V	0V
Vpp	Vcc	Vpgm	Vread	Vread
OSCs	Vcc	0V/Vcc oscillate	0V/Vcc oscillate	0V/Vcc oscillate

In Table 2, there is shown an example in which the word line WL1-i is selected in writing and reading.

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A power source voltage V_{cc} is typically set to 3 V, an erasing voltage V_{era} is typically set to 20 V, a writing voltage V_{pgm} is typically set to 18 V, a writing auxiliary voltage V_{pass} is typically set to 10 V, and a reading auxiliary voltage V_{read} is typically set to 3.5 V, a reading voltage V_{cgr} is typically set to 0 V, and a verify voltage V_{cgv} is typically set to 0.5 V. It is easy and possible to prepare a plurality of reading voltages and verify voltages for the multiplication of values.

FIG. 18 is a circuit diagram partially showing one example of a shift register circuit in the block selection circuit. In particular, a portion of the shift register circuit for generating, in particular, signals RA-i and RB-k is shown.

As shown in FIG. 18, when the reset signal RSTs is set to "H", a shift register SR-add is reset. When the clock signal CK0s is set to "H", an input signal IN is received to latch the input signal when the signal CK0s is set to "L"

FIG. 19 is a circuit diagram holistically showing one example of the shift register circuit in the block selection circuit. In particular, the whole shift register circuit for generating the signals RA-i and RB-K is shown.

The shift register circuit shown in FIG. 19 is provided adjacent to the circuit shown in FIG. 17 to

constitute the block selection circuit 26 together with the circuit shown in FIG. 17.

With the circuit shown in FIG. 19, it is possible to generate desired signals RA-I and RB-k by inputting address data signals RAs and RBs in synchronization with the clock signal CK0s. As a consequence, an arbitrary block can be selected.

FIG. 20 is a circuit diagram showing one example of a shift register circuit in a data circuit 27.

As shown in FIG. 20, when the reset signal RSTs is set to "H", the shift register SR-data is reset. When the clock signal CK1s is set to "H", the input signal IN is received to latch the input signal when the signal CK1s is set to "L". A node PBL is connected to the bit line BL. When the writing signal PGMs is set to "H", the latch circuit comprising inverters I23 and I24 and the bit line are linked to write data. At the reading and writing verify time, the voltage showing the data of the memory cell which appears in the bit line is such that a sense signal SENs is sensed at "H", and is latched to the latch circuit comprising the inverters I23 and I24.

FIG. 21 is a circuit diagram showing one example of the data circuit 27, the bit line circuit 28 and the bit line BL.

In the circuit shown in FIG. 21, the writing data signals IN0s and IN1s are input in synchronization with

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the clock signal CK1s, so that the desired writing data is set. Furthermore, the reading data signals OUT0s and OUT1s can be output in synchronization with the clock signal CK1s.

5 Either of the two bit lines BLe and BLo is selected with the bit line selection signals EVs and ODs. BLe is selected when the EVs is set to "H" and ODs is set to "L". BLo is selected when the EVs is set to "L" and the ODs is set to "H". The unselected bit
10 line is connected to a BS terminal when a precharge signal PREs is set to "H" with the bit line circuit 28.

 Furthermore, a potential of the selected bit line can be set in advance by using the bit line circuit 28. When the EVs is set "H" and ODs is set to "L", BLo is
15 connected to BS by setting the precharge signal PREs to "H". When the EVs is set to "L" and the ODs is set to "H", BLe is connected to the BS by setting the precharge signal PREs to "H". After that, when both the EVs and ODs are set to "L", the bit line to be
20 selected is precharged to the same potential as the BS. After this, data in the memory cell can be read by giving a potential to the word line.

 Each voltage at which the BLOCKi is selected is shown in Table 2. In Table 2, as described above,
25 there is shown an example in which the word line WL-i is selected in reading and writing.

FIG. 22 is a circuit diagram showing another

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example of the signal conversion circuit 31.

As shown in FIG. 22, an input protection element comprising a diode D0 and a resistor R0 may be connected to the terminal 8. FIG. 22 is a view showing an example of a chip selection signal CEO.

FIG. 23 is a circuit diagram showing one example of the source line circuit 29 and the well circuit 30.

In an example shown in FIG. 23, the source line circuit 29 and the well circuit 30 shares a portion of a circuit.

As shown in FIG. 23, the signal OSCs is synchronized with the oscillation signal generated in the package 4 to drive a pump circuit comprising NMOS transistors Qn31 and Qn32, a depletion type NMOS transistor Qd1. The chip selection signal CESn is set to "L" so that the p-type well 34 is linked in which the terminal Well and the memory cell are formed. Furthermore, the terminal SRC and the source line Source area linked.

Each voltage at which the BLOCKi is selected is shown in Table 2. As described above, Table 2 shows an example in which the word line WL1-1 is selected in the writing and reading.

FIG. 24 is a system diagram showing one example of a system of the nonvolatile memory device according to the first embodiment of the present invention.

As shown in FIG. 24, one package is 4 controls a

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plurality of NAND flash memories 5 via the wiring 6. A control circuit can be eliminated from the individual NAND flash memory 5 by sharing the control circuit in this manner with the result that a NAND flash memory 5 having a small chip size can be created. For example, as a result of this, a cheap flash memory system as a whole can be obtained.

The inside of the package 4 can largely divided into two portions. A NAND flash interface 37 is a summary of the data input and output buffer 13, the control signal buffer 14 and the state machine 15 shown in FIG. 8. A residual portion shown in FIG. 8 is a NAND flash control engine 36.

The package 4 is controlled under the file control system such as a computer or the like via the terminal 3.

In this manner, the nonvolatile semiconductor memory device or nonvolatile semiconductor memory system according to the first embodiment of the present invention includes, for example, a first semiconductor substrate and a second semiconductor substrate. For example, on the first semiconductor substrate, a memory cell array including a plurality of nonvolatile semiconductor memory cells, a plurality of bit lines electrically connected to the memory cell array, a plurality of word lines electrically connected to the memory cell array, a plurality of input terminals, and

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a plurality of transfer gate transistors having each of one ends connected to the plurality of word lines and having each of the other ends connected to the plurality of input terminals are provided. For example, on the second semiconductor substrate, a plurality of output terminals electrically connected to the plurality of input terminals, and a word line control circuit electrically connected to the plurality of output terminals for controlling a plurality of word lines are provided.

Furthermore, the nonvolatile semiconductor memory device or nonvolatile semiconductor memory system according to the first embodiment of the present invention includes, for example, the first semiconductor substrate and the second semiconductor substrate. For example, on the first semiconductor substrate, a memory cell array including a plurality of nonvolatile semiconductor memory cells, a plurality of bit lines electrically connected to the memory cell array, a plurality of word lines electrically connected to the memory cell array, a plurality of input terminals, and a plurality of transfer gate transistors having each of one ends electrically connected to the plurality of word lines and having each of the other ends electrically connected to the plurality of input terminals are provided. For example, on the second semiconductor substrate, a plurality of output

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output terminals electrically connected to the plurality of input terminals, and a word line control circuit electrically connected to the plurality of output terminals for controlling the plurality of word lines are provided.

Furthermore, as another configuration of the nonvolatile semiconductor memory device or nonvolatile semiconductor memory device system according to the first embodiment, the following can be given.

(1) The first semiconductor substrate and the second semiconductor substrate are stacked on each other.

(2) The first semiconductor substrates are provided in plurality and the first semiconductor substrates and the second semiconductor substrate are stacked on each other.

FIGS. 25A and 25B show such a modification of the nonvolatile semiconductor memory or memory system.

As FIG. 25A shows, a semiconductor substrate 9 is laid on a stack of eight semiconductor substrates 12-0 to 12-7. This structure is different from the first embodiment in which the package 4 is stacked on the one of the packages 5.

The first embodiment may comprise only one package 5. Similarly, the modification shown in FIG. 25A may comprise only one semiconductor substrate 12. In this case, the semiconductor substrate 9 and the

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semiconductor substrate 12 are combined, in back-to-back position as is illustrated in FIG. 25B. Similarly, the package 4 and the package 5 are combined, in back-to-back position, in the first embodiment.

5 As has been described above, in the nonvolatile semiconductor memory device or nonvolatile semiconductor memory system according to the first embodiment of the present invention, a large number of control circuits can be eliminated from a plurality of
10 flash memory chips. Then, a cheap flash memory system can be obtained by sharing the control circuit in a single or a plurality of flash memory chips. Furthermore, for example, when packaged or wired as shown in FIG. 2, the flash memory system can be used as
15 one flash memory device.

Furthermore, the nonvolatile semiconductor memory device or nonvolatile semiconductor memory system according to the first embodiment of the present invention can be modified in various ways with the
20 example shown in another form of the embodiment being set as a representative example.

(Second Embodiment)

FIG. 26 is a system view showing a nonvolatile semiconductor memory device system according to a
25 second embodiment of the present invention.

As shown in FIG. 26, inside of the package 4, there are provided a file management engine 38 for

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managing a relation of a data file and an address of
the memory cell array 25 and a network interface 39
corresponding to a network protocol as an interface
with the outside. The package 4 can be directly linked
5 to the network such as the internet or the like via the
terminal 3 or the like.

For example, the network interface 39 corresponds
to the TCP/IP (transmission control protocol/internet
protocol) which is a main stream in the internet.

10 Furthermore, for example, the network interface 39
corresponding, for example, to the TCP/IP can be
connected with the ftp (file transfer protocol). As a
consequence, the nonvolatile semiconductor memory
device according to the present invention can be linked
15 to the network as an FTP site. Furthermore, the
network interface 39 is made linkable with an anonymous
ftp (file transfer protocol) so that the network
interface 39 can be connected more simply to the
network. The network interface 39 can be also
20 connected with the PPP (point-to-point protocol). Thus,
the nonvolatile semiconductor memory device or
nonvolatile semiconductor memory device system
according to the second embodiment of the present
invention is convenient in that the device or the
25 system can be linked to the network via a telephone
circuit.

FIG. 27 is a view showing a relation between the

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network and the nonvolatile semiconductor memory device shown in FIG. 26 network is sealed in the package 1.

As shown in FIG. 27, the data servers 43-0 through 43-4 and a software download machine 41 are linked via a TCP/IP protocol network 42. Software (for example, music source) required for the package 1 inserted into the software download machine 41 is held with the network 42 by using the FTP. The package 1 is pulled out from the software download machine 41 so that music or the like can be enjoyed with a portable music player 40, or the like.

FIG. 28 is a view showing another relation between the network and the nonvolatile semiconductor memory device shown in FIG. 26 which is sealed in the package 1.

As shown in FIG. 28, a data server 46 corresponding to the TCP/IP protocol and a telephone 44 are linked via a telephone circuit 45. Software (for example, music source) required for the package 1 inserted into the package 1 inserted into the telephone 44 is held from the data server 46 by using the PPP. The package 1 is pulled out from the telephone so that music or the like can be enjoyed with the portable music player 40 or the like.

Furthermore, it is possible to connect the single body to the network by adding a power source unit (battery or the like) and an input device to the

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package 1.

In this manner, the nonvolatile semiconductor memory device or nonvolatile semiconductor memory system according to the second embodiment of the present invention includes a memory having a memory cell array including a plurality of nonvolatile semiconductor memory cells, a control portion for controlling the memory, a network interface corresponding to a network protocol which can be connected to the network, a file management portion connected to the network interface for managing a relation between a data file given from the network and an address of the memory cell array, and a memory interface connected to the file management portion for converting a signal given from the network to a signal which can be used with the control portion.

Furthermore, the nonvolatile semiconductor memory device or nonvolatile semiconductor memory device system according to the second embodiment of the present invention can be appropriately combined with the first embodiment.

The nonvolatile semiconductor memory device or nonvolatile semiconductor memory device system in one example of the combination is provided with a first semiconductor substrate and a second semiconductor substrate. For example, on the first semiconductor substrate, a memory having a memory cell including a

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plurality of nonvolatile semiconductor memory cells is provided. For example, on the second semiconductor substrate, a control portion for controlling the memory, a network interface corresponding to the network
5 protocol which can be connected to the network, and a file management portion connected to the network interface for managing a relation between a data file given from the network and an address of the memory cell array, and a memory interface connected to the
10 file management portion for converting a signal given from the network to a signal which can be used at the control portion are provided.

In this manner, according to the second embodiment of the present invention, there can be provided one
15 example of a nonvolatile semiconductor memory device or nonvolatile semiconductor memory device system provided with a file control system having an interface having a high affinity with many computer systems.

So far, the present invention has been explained
20 according to the first and the second embodiments. However, the present invention is not limited to the embodiments. In the practice of the invention, the invention can be modified in various ways within the scope of not departing from the gist of the present
25 invention.

Furthermore, each of the embodiments includes various stages of the invention. With an appropriate

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combination of a plurality of constituent elements,
various stages of the invention can be extracted.

Additional advantages and modifications will
readily occur to those skilled in the art. Therefore,
5 the invention in its broader aspects is not limited to
the specific details and representative embodiments
shown and described herein. Accordingly, various
modifications may be made without departing from the
spirit or scope of the general inventive concept as
10 defined by the appended claims and their equivalents.

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